PbS near-infrared detector Multi-Single-Pixel thin-film encapsulated



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Features

- Wire-bonded on PCB
- High durability for rugged operation
- Very high sensitivity
- Room temperature operation

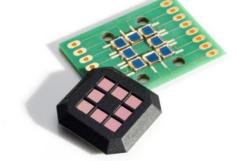
Applications

- Spectroscopy
- Gas detection and analysis
- Flame monitoring
- Flame and spark detection
- Temperature measurement
- Moisture measurement
- Rapid prototyping

Electrical and optical characteristics per pixel

Type No.	Active area [mm x mm]	Peak responsivity S [V/W]	
		Тур.	Min.
PbS010010BC	1 x 1	8 · 10 ⁵	5.6 · 10 ⁵
PbS020020BC	2 x 2	4 · 10 ⁵	2.8 · 10 ⁵
PbS030030BC	3 x 3	3 · 10 ⁵	1.8 · 10 ⁵
PbS060060BC	6 x 6	1.4 · 10 ⁵	0.9 · 10 ⁵
PbS010050BC*	1 x 5	$3.5 \cdot 10^{5}$	2 · 10 ⁵

^{*} Dark resistance $R_D[M\Omega] = 0.05 - 1$



- Measured with 1550 nm LED, incident power 16 μW/cm²
- Measured in a voltage divider circuit with 1 $M\Omega$ load resistor
- Photo responsivity and detectivity calculated for a voltage divider circuit with matched resistance and 50 V/mm

Element	Peak wave-	20% cut-off	Peak D*		Time constant	Dark resistance R _D
temperature	length λ₽	wavelength λ _C	(620 Hz, 1 Hz)		[µs]	[MΩ]
[°C]	[µm]	[µm]	[cm·Hz½/W]			
	Тур.	Typ.	Тур.	Min.	Тур.	
	. 7 P	. 7 P			. 7 P	
22	2.7	2.9	$1 \cdot 10^{11}$	$0.8 \cdot 10^{11}$	200	0.3 - 3

Mechanical characteristics

Number of lines 1 - 3 Number of pixels 2 - 8

Minimum pixel width 1000 um Minimum pixel height 1000 μm

Contact

Please contact us for an individual design: info@trinamix.de

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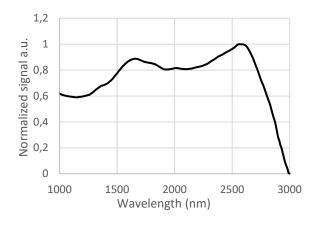
67063 Ludwigshafen Germany

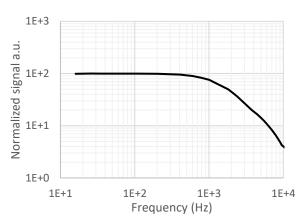
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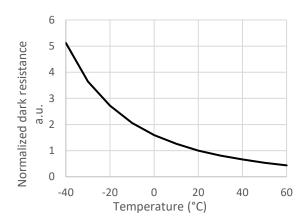


Typical spectral response per pixel Typical frequency response per pixel





Typical resistance change over temperature



Storage

• Storage temperature: -55°C to +70°C

conditions of sale.

- Exposure to UV light results in permanent damage
- Prolonged exposure to visible light results in temporary low dark resistance

Handling

- Active area is scratch sensitive, protect top surface from any mechanical contact
- Ensure dust-free environment for device handling
- Operating temperature: -30°C to +70°C

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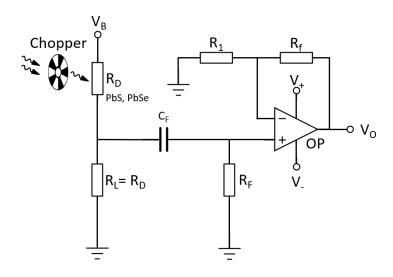


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Options

- Individual housing
- Integrated filters
- Individual PCB
- Evaluation Kit available

Exemplary circuit



Bias voltage

√o: Output voltage

R_D: Dark resistance of the detector

R_L: Load resistorC_F: Filter capacitorR_F: Filter resistor

R_f: Feedback resistor

R₁: Gain resistor

Regulatory

For the use of trinamiX PbS and PbSe infrared photodetectors in medical devices, monitoring and control instruments and consumer applications RoHS exemptions apply.

For automotive applications trinamiX PbS and PbSe infrared photodetectors fall under ELV exemption.